

Notice of Allowability

Application No.

10/072.855

Examiner

Thinh T Nguyen

Applicant(s)

KARASAWA ET AL.

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-- **Th MAILING DATE of this communication appears in the cover sheet with the corresponding address--**

All claims being allowable, PROSECUTION ON THE MERITS IS (OR REMAINS) CLOSED in this application. If not included herewith (or previously mailed), a Notice of Allowance (PTOL-85) or other appropriate communication will be mailed in due course. **THIS NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RIGHTS.** This application is subject to withdrawal from issue at the initiative of the Office or upon petition by the applicant. See 37 CFR 1.313 and MPEP 1308.

1. ☒ This communication is responsive to 8/7/2003.
 2. ☒ The allowed claim(s) is/are 1-15.
 3. ☒ The drawings filed on 06 February 2002 are accepted by the Examiner.
 4. ☒ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
 - a) ☒ All b) ☐ Some* c) ☐ None of the:
 1. ☒ Certified copies of the priority documents have been received.
 2. ☐ Certified copies of the priority documents have been received in Application No. _____.
 3. ☐ Copies of the certified copies of the priority documents have been received in this national stage application from the International Bureau (PCT Rule 17.2(a)).
- * Certified copies not received: _____.
5. ☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. § 119(e) (to a provisional application).
 - a) ☐ The translation of the foreign language provisional application has been received.
 6. ☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. §§ 120 and/or 121.

Applicant has THREE MONTHS FROM THE "MAILING DATE" of this communication to file a reply complying with the requirements noted below. Failure to timely comply will result in ABANDONMENT of this application. **THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.**

7. ☐ A SUBSTITUTE OATH OR DECLARATION must be submitted. Note the attached EXAMINER'S AMENDMENT or NOTICE OF INFORMAL PATENT APPLICATION (PTO-152) which gives reason(s) why the oath or declaration is deficient.
8. ☐ CORRECTED DRAWINGS must be submitted.
 - a) ☐ including changes required by the Notice of Draftsperson's Patent Drawing Review (PTO-948) attached
 - 1) ☐ hereto or 2) ☐ to Paper No. _____.
 - b) ☐ including changes required by the proposed drawing correction filed _____, which has been approved by the Examiner.
 - c) ☐ including changes required by the attached Examiner's Amendment / Comment or in the Office action of Paper No. _____.

Identifying indicia such as the application number (see 37 CFR 1.84(c)) should be written on the drawings in the front (not the back) of each sheet.

9. ☐ DEPOSIT OF and/or INFORMATION about the deposit of BIOLOGICAL MATERIAL must be submitted. Note the attached Examiner's comment regarding REQUIREMENT FOR THE DEPOSIT OF BIOLOGICAL MATERIAL.

Attachment(s)

- 1 ☐ Notice of References Cited (PTO-892)
- 3 ☐ Notice of Draftsperson's Patent Drawing Review (PTO-948)
- 5 ☒ Information Disclosure Statements (PTO-1449), Paper No. 11.
- 7 ☐ Examiner's Comment Regarding Requirement for Deposit of Biological Material
- 2 ☐ Notice of Informal Patent Application (PTO-152)
- 4 ☐ Interview Summary (PTO-413), Paper No. _____.
- 6 ☐ Examiner's Amendment/Comment
- 8 ☒ Examiner's Statement of Reasons for Allowance
- 9 ☐ Other


David Neims
Supervisory Patent Examiner
Technology Center 2800

DETAILED ACTION

Reason for allowance

1. Claims 1-15 are allowed. The following is an examiner's statement of reason for allowance:

A/ Applicant filing of the Terminal Disclaimer has overcome the double patenting rejection of claims 1-15.

B/ Claims 1-15 are allowed because the prior fails to teach a structure of a:

-- "A semiconductor device comprising:

a first gate-gate electrode layer including a gate electrode of a first load transistor and a gate electrode of a first driver transistor;

a second gate-gate electrode layer including a gate electrode of a second load transistor and a gate electrode of a second driver transistor; a first drain-drain wiring layer which forms a part of a connection layer that electrically connects a drain region of the first load transistor and a drain region of the first driver transistor; a second drain-drain wiring layer which forms a part of a connection layer that electrically connects a drain region of the second load transistor and a drain region of the second driver transistor; a first drain-gate-wiring layer, which forms a part of a connection layer that electrically connects the first gate-gate electrode layer and the second drain-drain wiring layer; and a second drain-gate wiring layer which forms a part of a connection l

layer that electrically connects the second gate-gate electrode layer and the first drain-drain wiring layer, wherein the first drain-gate wiring layer and the second drain-gate wiring layer are located in different layers, respectively, and wherein a width of the first gate-gate electrode layer in the first load transistor is larger than the width of the first gate-gate electrode layer in the first driver transistor. "

In claim 1.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance".

Conclusion

2. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Thinh T Nguyen whose telephone number is 703-305-0421. The examiner can normally be reached on Monday-Friday 8:30am-5:00pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, David Nelms can be reached on 703-308-4910. The fax phone numbers for

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the organization where this application or proceeding is assigned are (703) 872-9306 for regular communications and (703) 872-9319 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0956.

Thinh T Nguyen 

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David Nellis
Supervisory Patent Examiner
Technology Center 2800